

FIG. 2

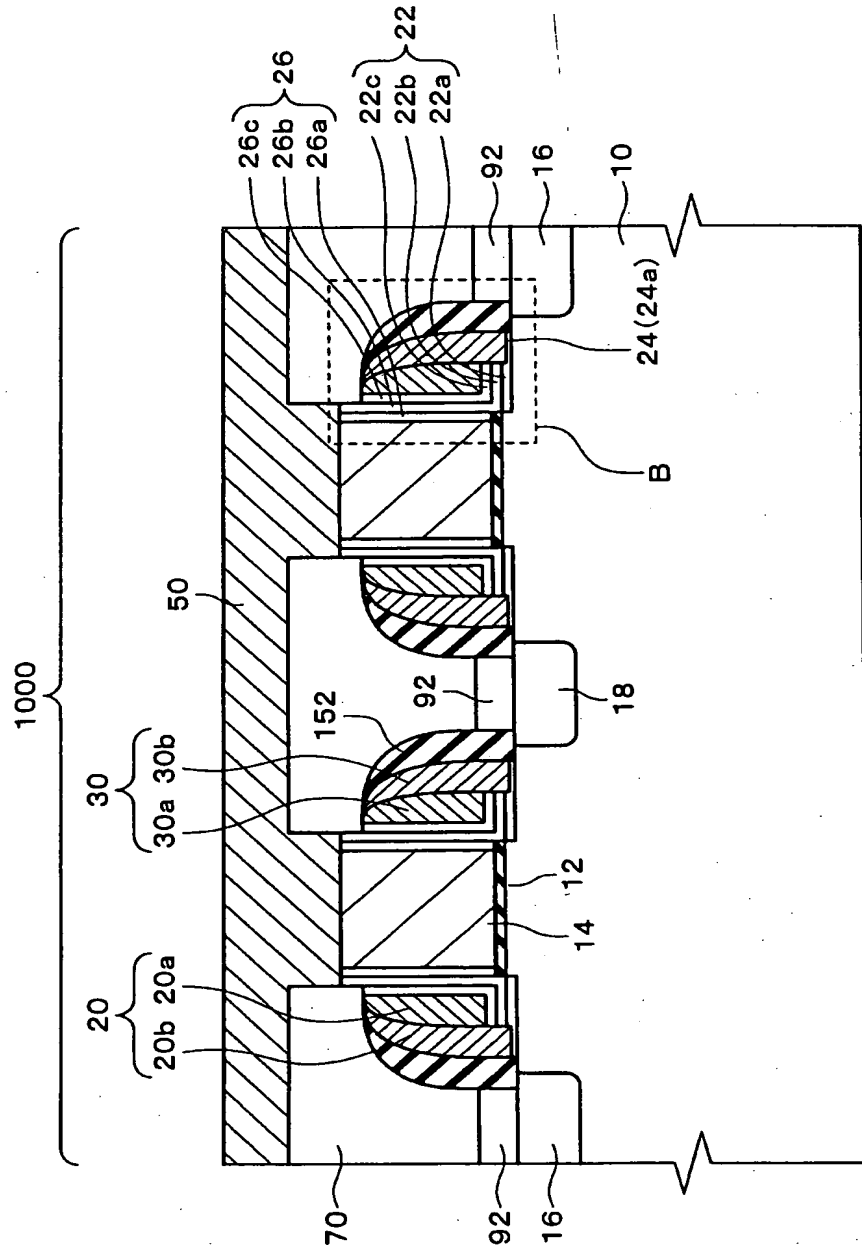


FIG. 3

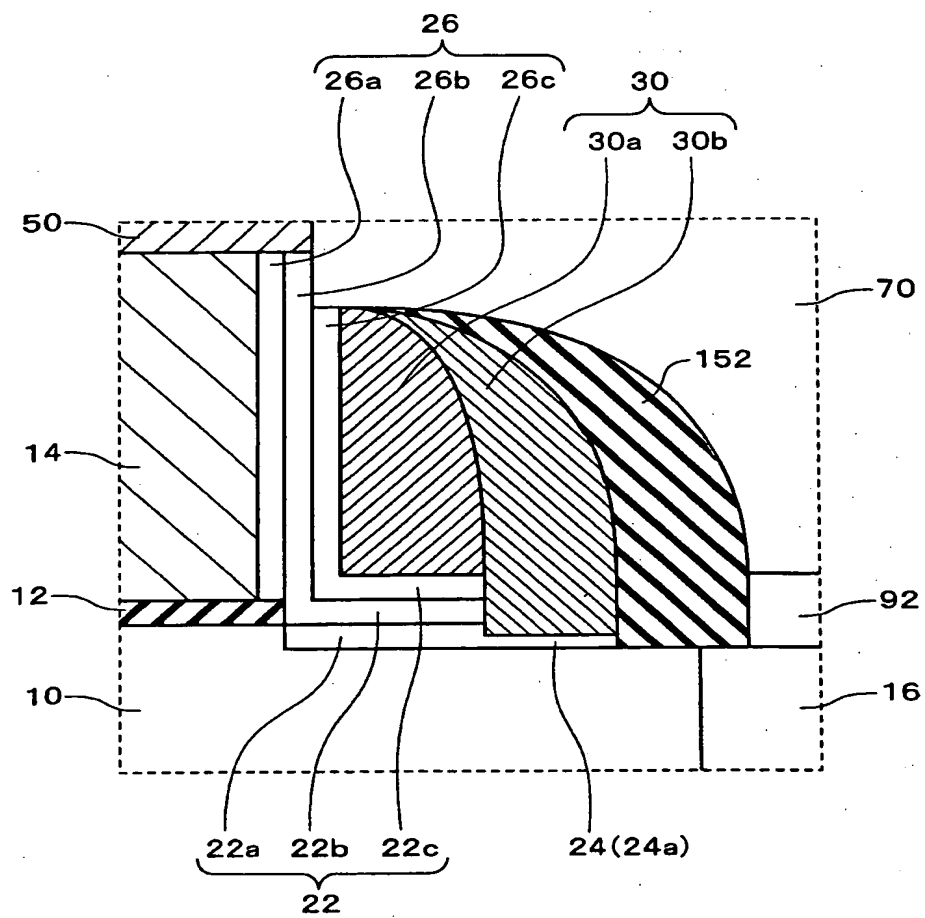


FIG. 4

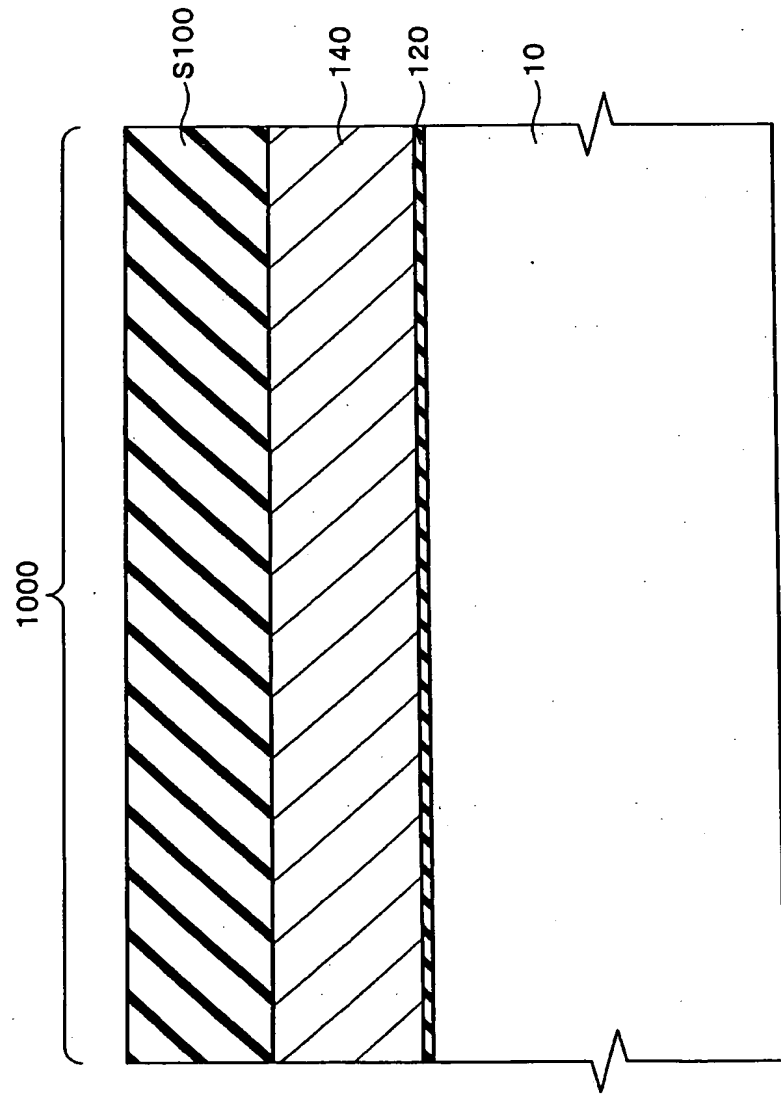


FIG. 5

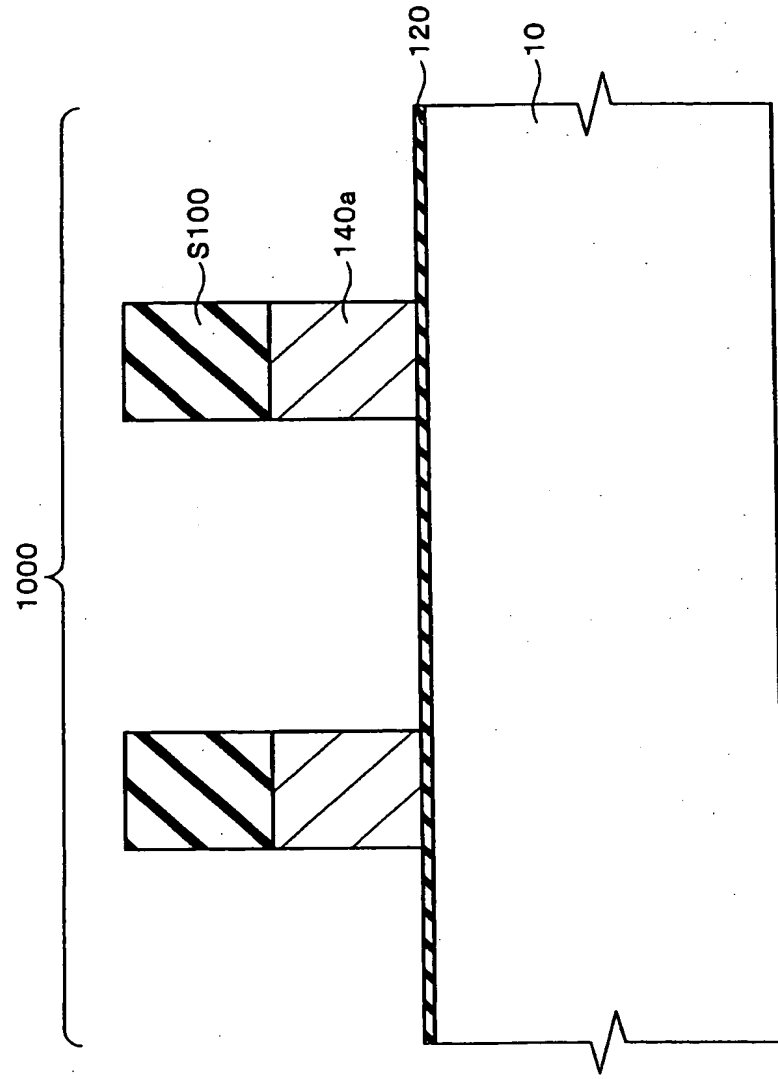


FIG. 6

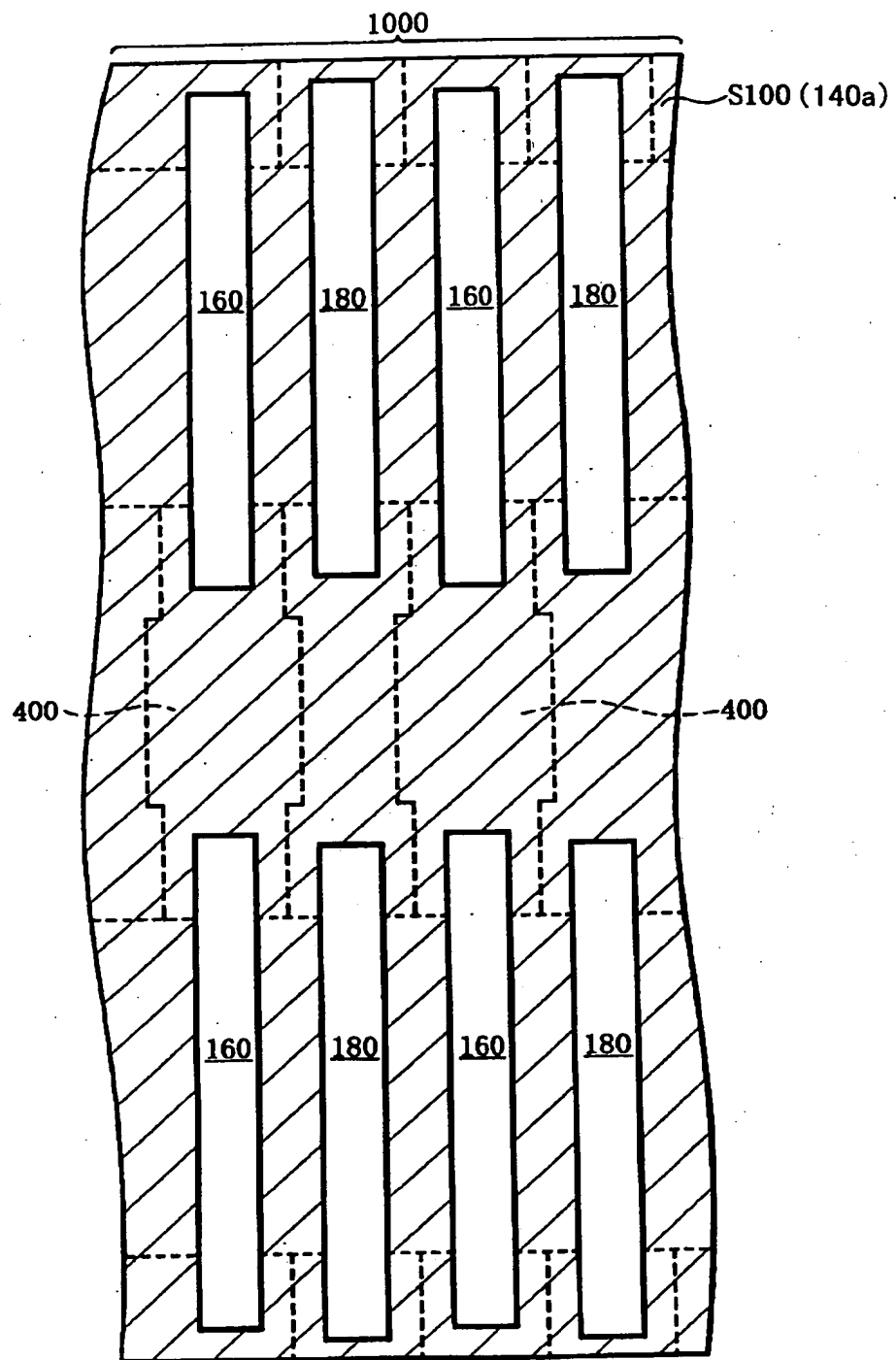


FIG. 7

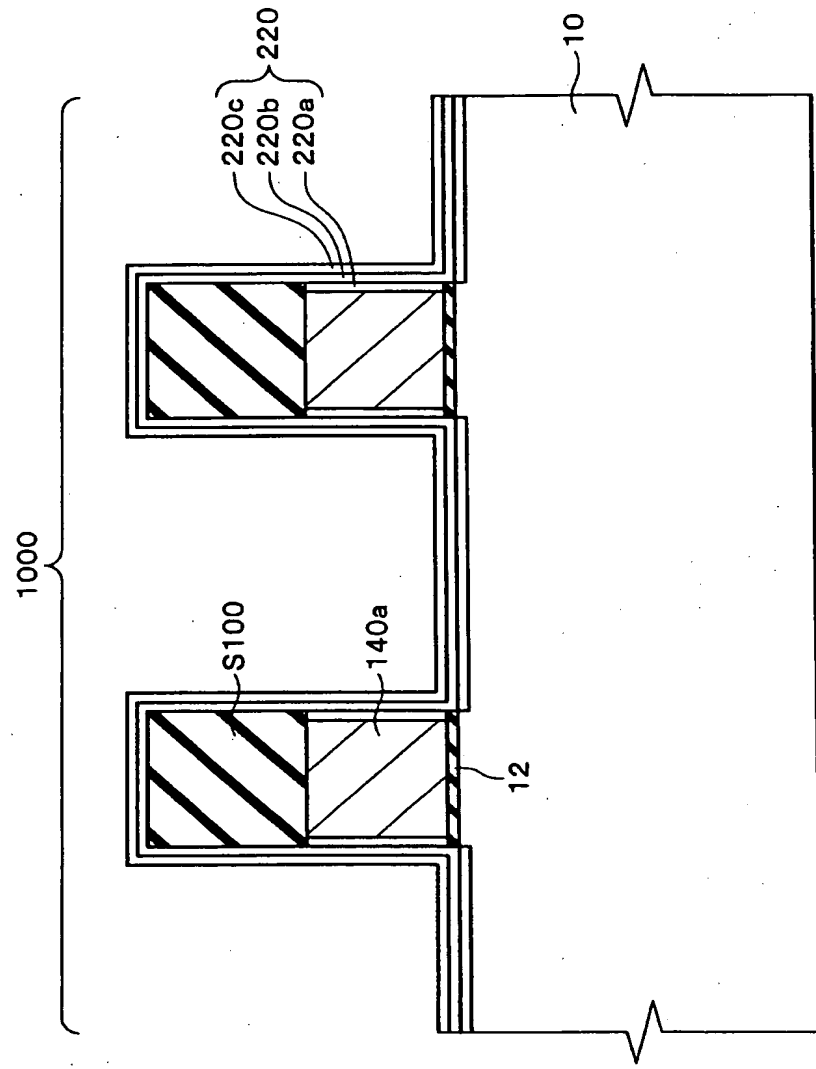


FIG. 8

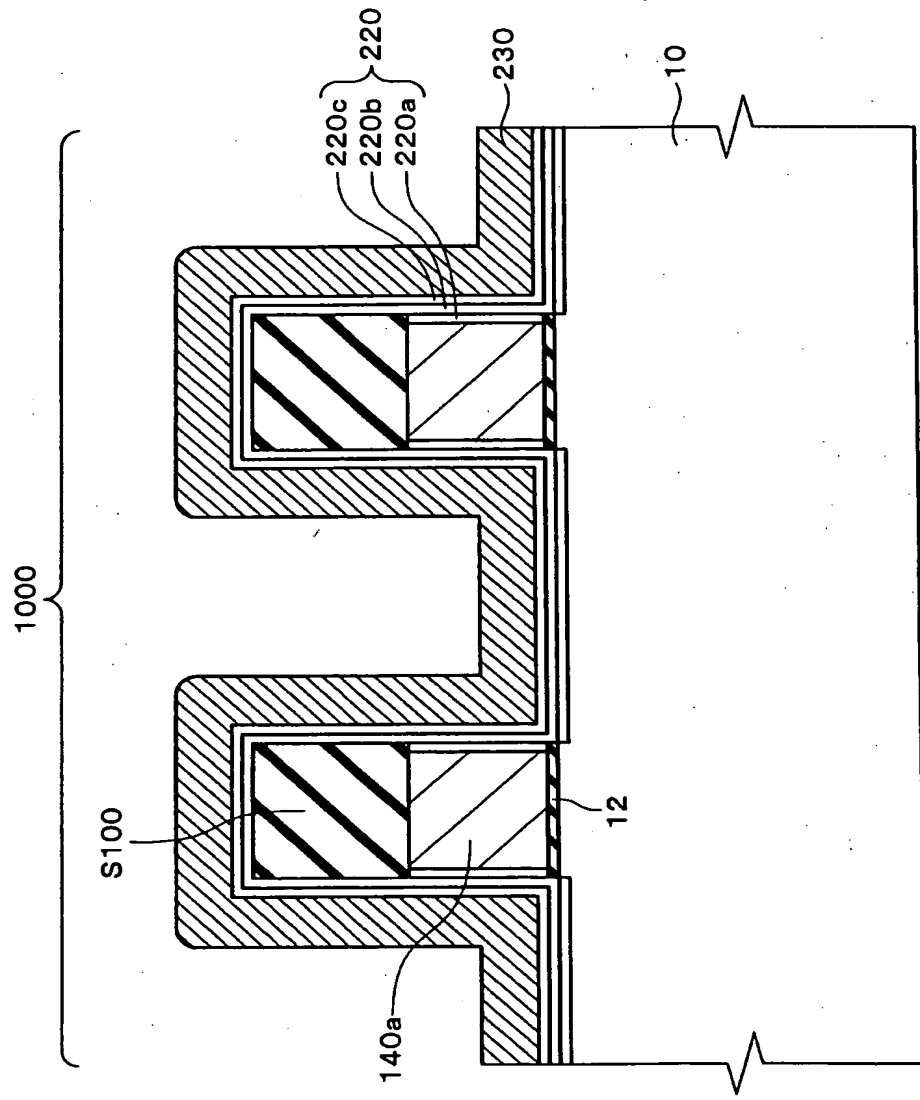


FIG. 9

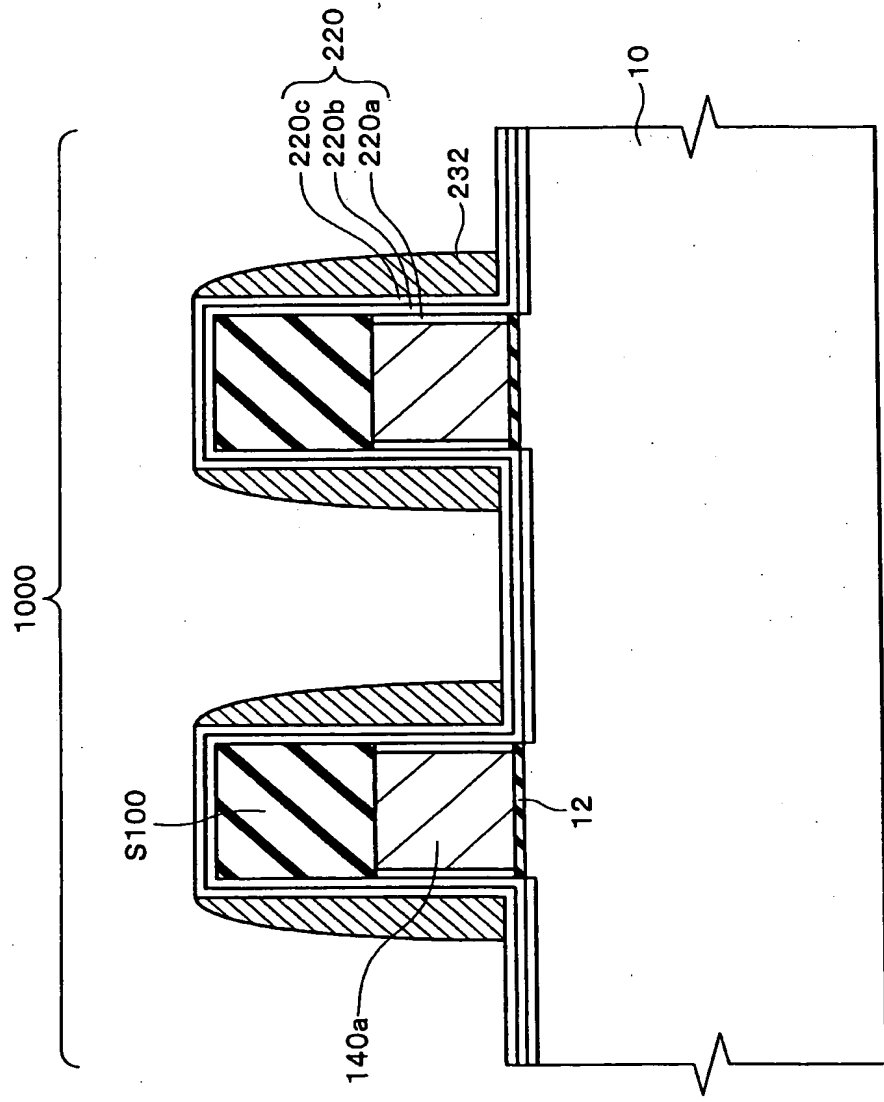


FIG. 10

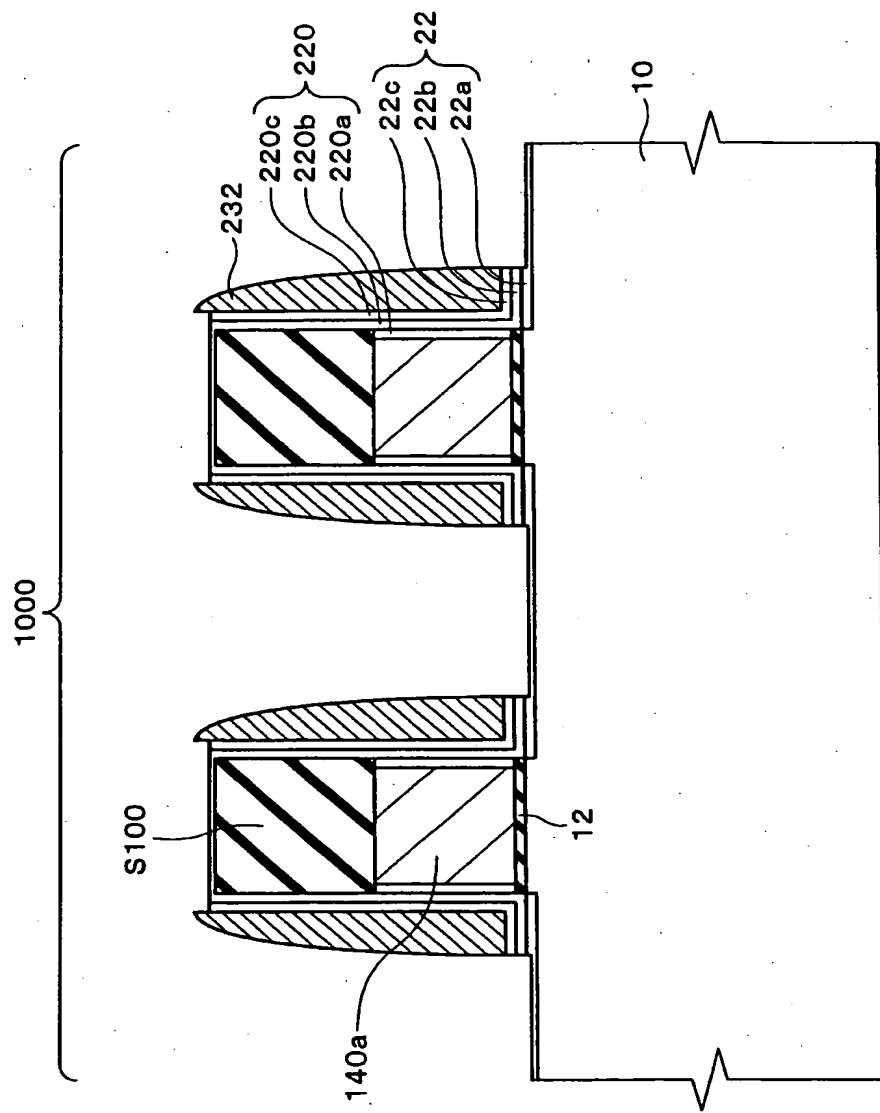
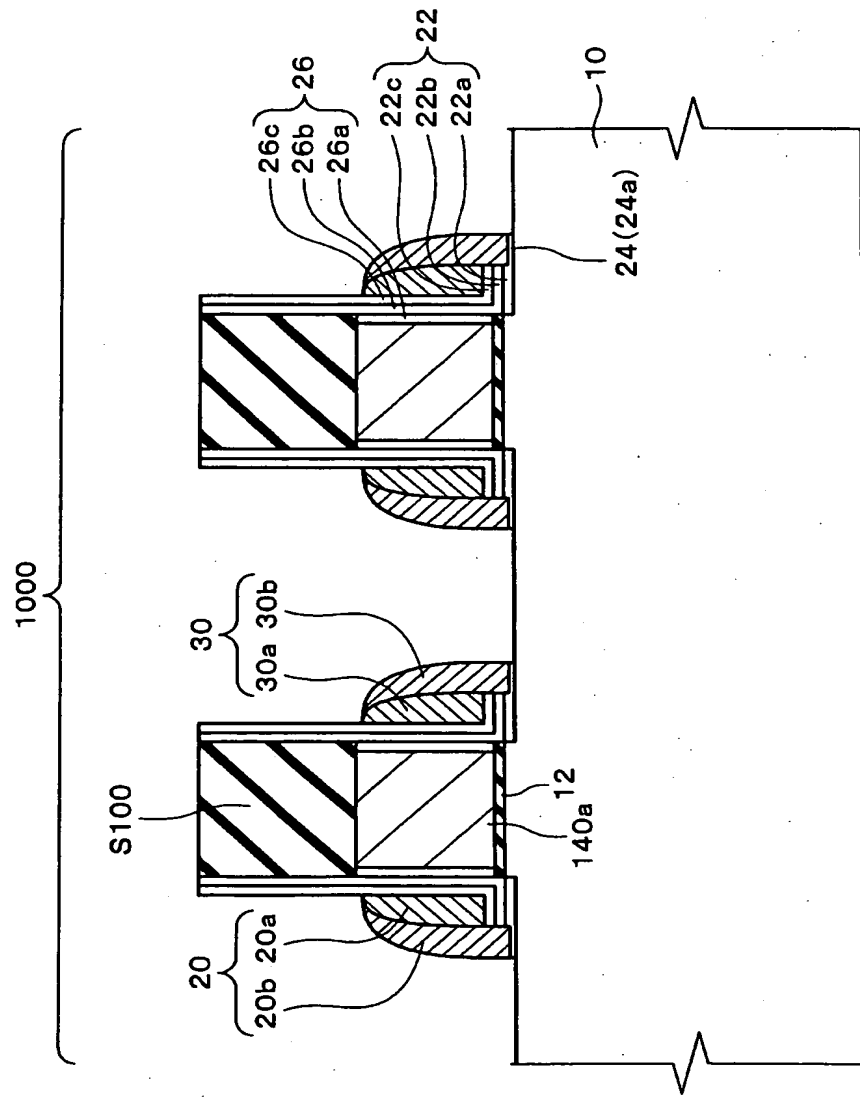
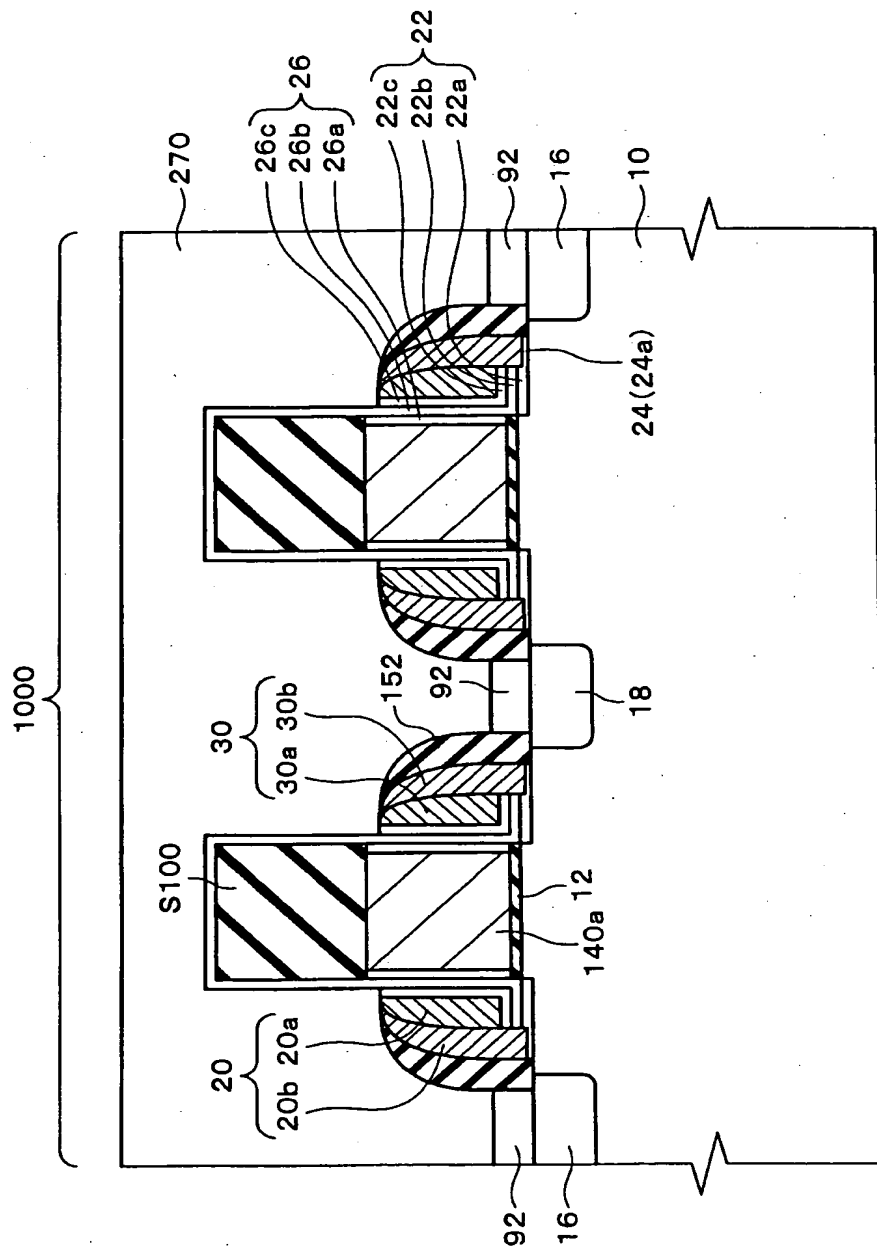


FIG. 11



[illegible]

This cross-sectional diagram illustrates a semiconductor device with multiple layers and components. The device is shown in a cross-section with a central core and side regions. The central core is divided into three main sections, each containing a different material or layer. The top layer is labeled 1000, and the bottom layer is labeled 100. The central core is labeled 30, and the side regions are labeled 20. The central core is further divided into three sections, each containing a different material or layer. The top layer is labeled 1000, and the bottom layer is labeled 100. The central core is labeled 30, and the side regions are labeled 20. The central core is further divided into three sections, each containing a different material or layer. The top layer is labeled 1000, and the bottom layer is labeled 100. The central core is labeled 30, and the side regions are labeled 20.

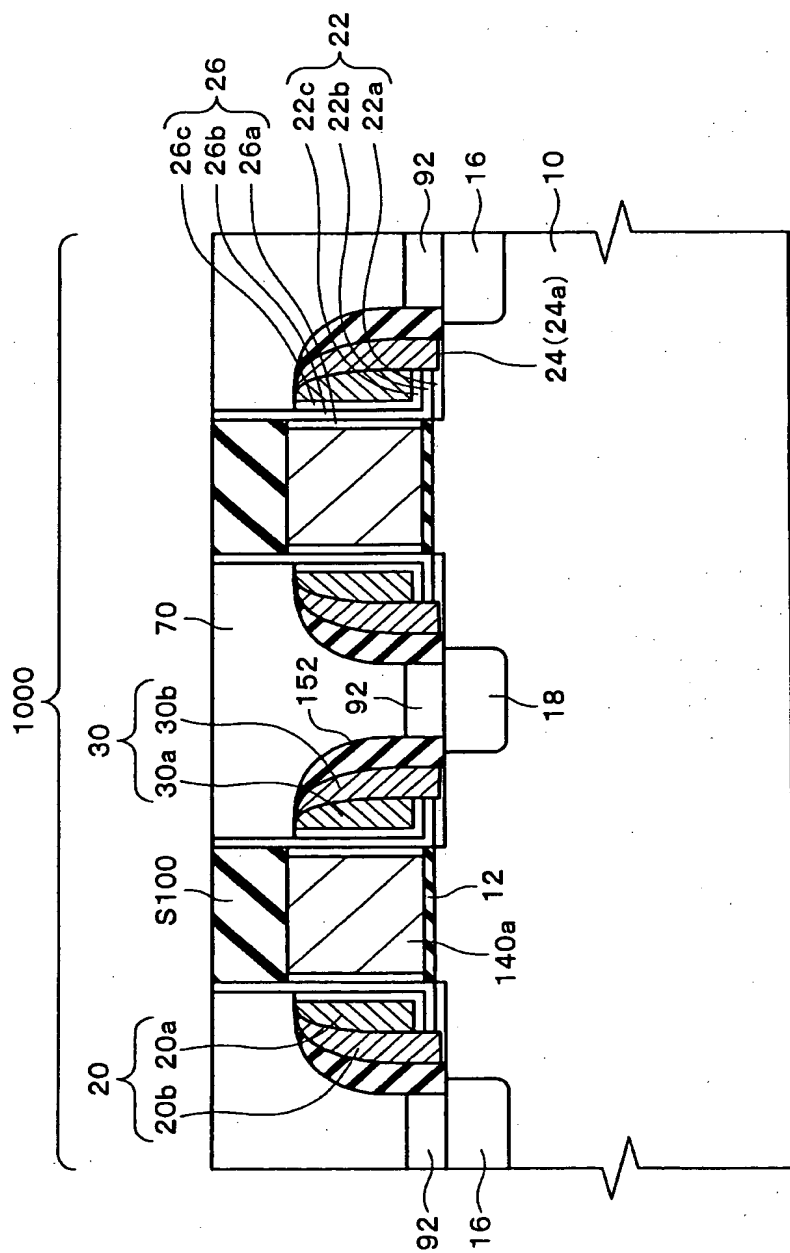


FIG. 14

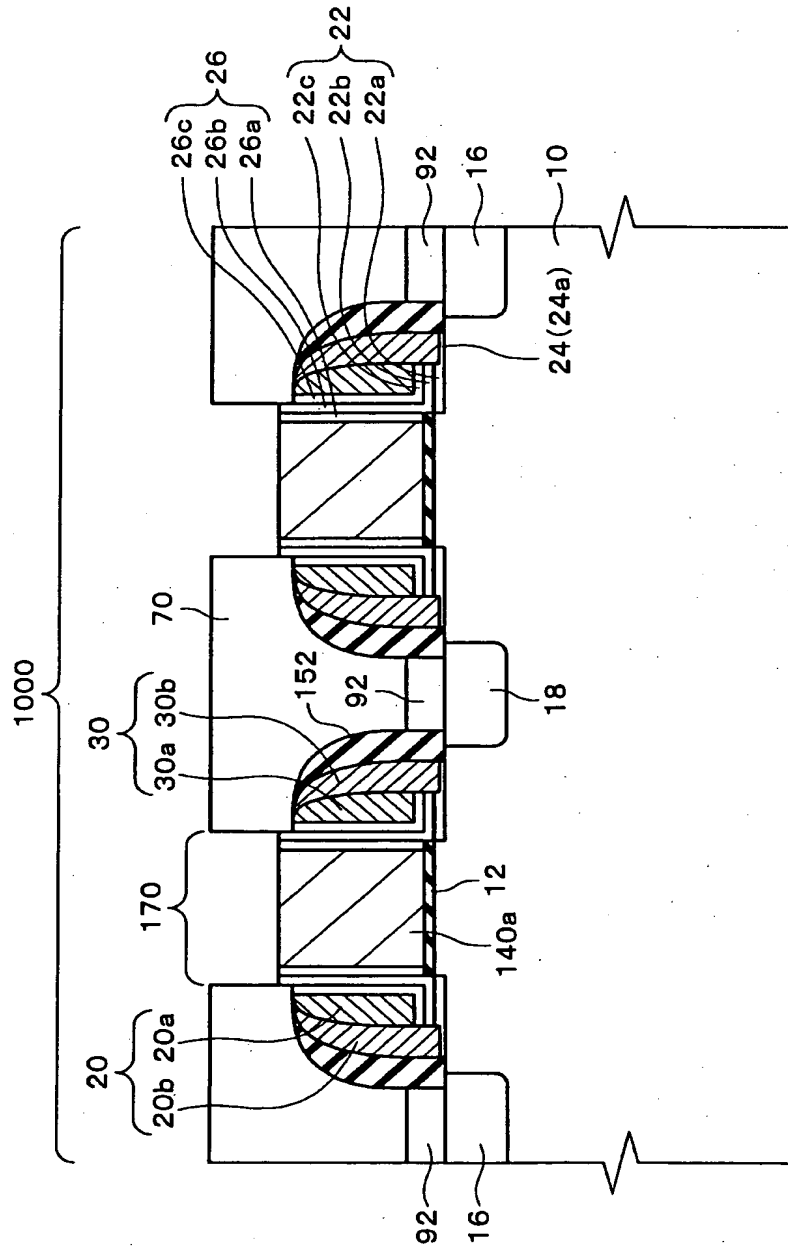


FIG. 15

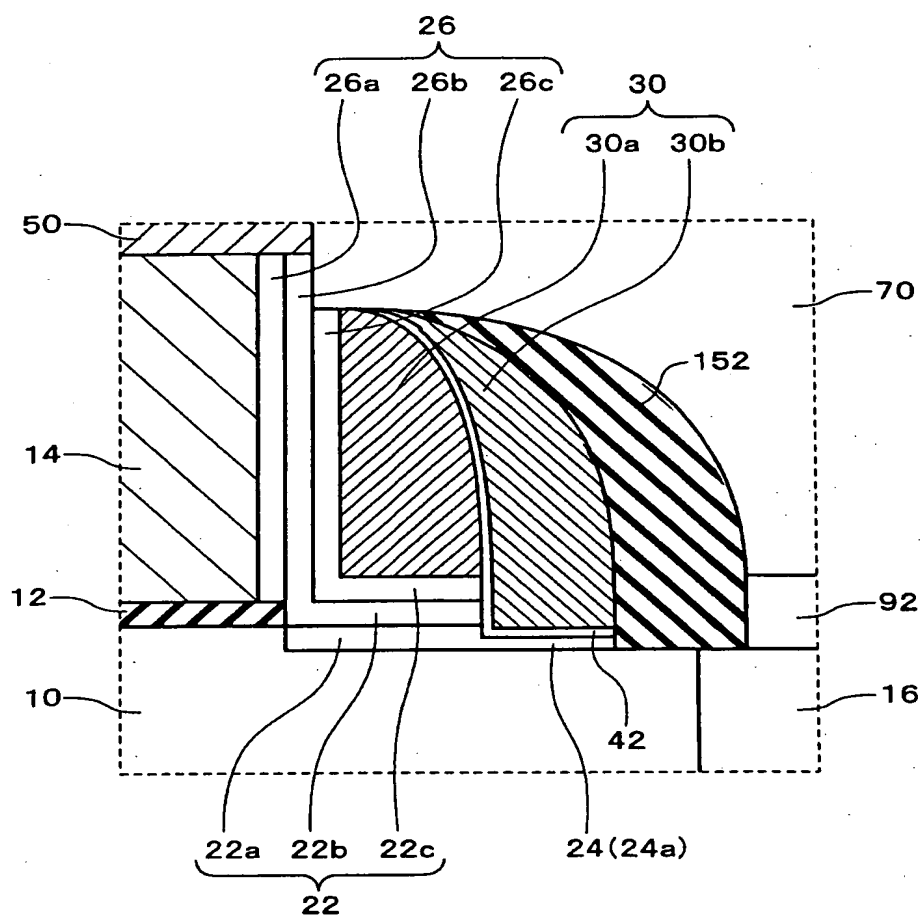


FIG. 16

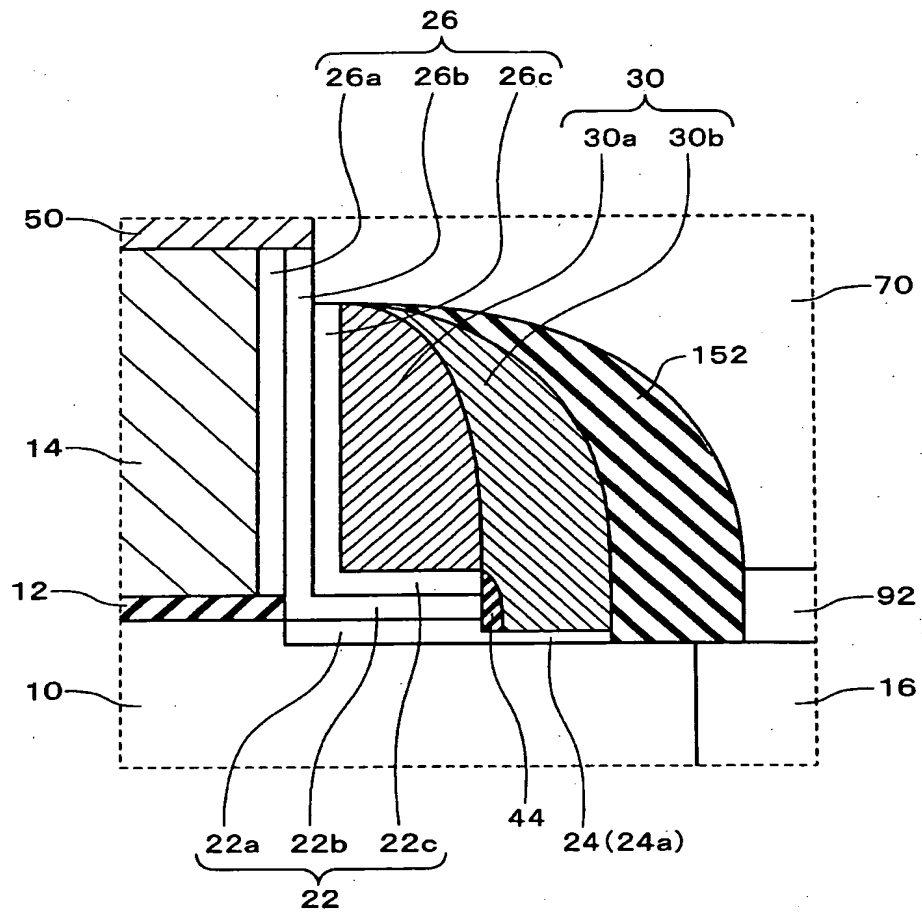


FIG. 17

PRIOR ART

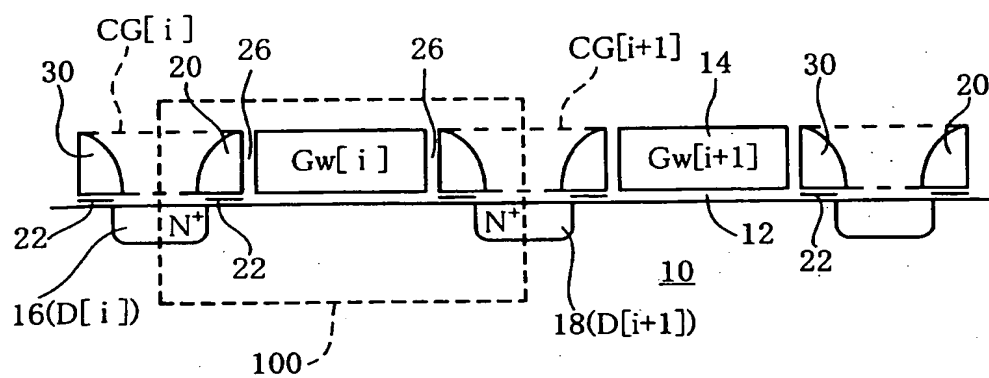


FIG. 18

